

Q2
cont

substrate (1) and provided thereon a bandpass filter of bulk acoustic wave resonators and a notch filter, by which method

B2
provided

- a second electrode (5), a piezoelectric layer (4), and a first electrode (3) are provided on a carrier layer and are structured such that at least one resonator unit, a capacitor, and an inductance are created,
- a reflection element (2) is deposited on those portions of the first electrode (3) which belong to the resonator unit,
- a substrate (1) is fastened on the entire assembly, and the carrier layer is removed.

Fig 13
B2

13. (New) A filter arrangement as claimed in claim 1, characterized in that the bandpass filter and the notch filter are thin-film filters.

14. (New) The method of claim 8, wherein said carrier layer consists of a ceramic material, a ceramic material with a planarizing layer of glass, a glass-ceramic material, silicon, GaAs or sapphire.

15. (New) The method of claim 8 wherein said carrier layer is removed mechanically.

16. The method of claim 8 wherein said carrier layer is removed chemically.

IN THE DRAWINGS:

dashed line and designated by "Si" so as to overcome the deficiency in the drawings.